

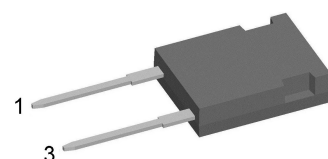
HiPerDynFRED

V_{RRM}	=	600 V
I_{FAV}	=	30 A
t_{rr}	=	35 ns

High Performance Dynamic Fast Recovery Diode
 Extreme Low Loss and Soft Recovery
 Single Diode

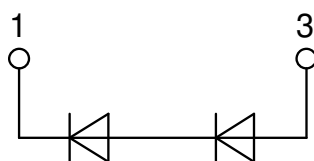
Part number

DPH30IS600HI



Backside: isolated

 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: ISOPLUS247

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

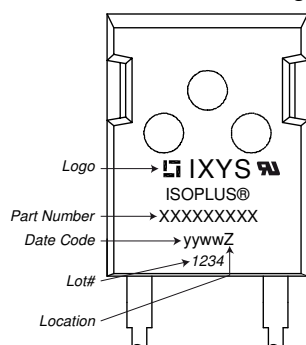
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Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				600	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				600	V
I_R	reverse current, drain current	$V_R = 600\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1	μA
		$V_R = 600\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			0.2	mA
V_F	forward voltage drop	$I_F = 30\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			2.48	V
		$I_F = 60\text{ A}$				3.02	V
		$I_F = 30\text{ A}$	$T_{VJ} = 150^{\circ}\text{C}$			1.89	V
		$I_F = 60\text{ A}$				2.45	V
I_{FAV}	average forward current	$T_C = 140^{\circ}\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 175^{\circ}\text{C}$			30	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^{\circ}\text{C}$		1.10	V
r_F	slope resistance					12.6	m Ω
R_{thJC}	thermal resistance junction to case					0.55	K/W
R_{thCH}	thermal resistance case to heatsink				0.3		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				285	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$	$T_{VJ} = 45^{\circ}\text{C}$			450	A
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		30		pF
I_{RM}	max. reverse recovery current	$I_F = 30\text{ A}; V_R = 400\text{ V}$ $-di_F/dt = 200\text{ A}/\mu\text{s}$		$T_{VJ} = 25^{\circ}\text{C}$		3	A
				$T_{VJ} = 125^{\circ}\text{C}$		8	A
t_{rr}	reverse recovery time			$T_{VJ} = 25^{\circ}\text{C}$		35	ns
				$T_{VJ} = 125^{\circ}\text{C}$		65	ns

Package ISOPLUS247				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				70	A
T _{VJ}	virtual junction temperature			-55		175	°C
T _{op}	operation temperature			-55		150	°C
T _{stg}	storage temperature			-55		150	°C
Weight					6		g
F _C	mounting force with clip			20		120	N
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal		5.4			mm
d _{Spb/Apb}		terminal to backside		4.1			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA	3600			V
		t = 1 minute		3000			V

Product Marking



Part description

D = Diode
 P = HiPerFRED
 H = HiPerDyn
 30 = Current Rating [A]
 IS = Single Diode
 600 = Reverse Voltage [V]
 HI = ISOPLUS247 (2)

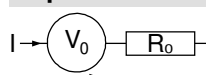
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DPH30IS600HI	DPH30IS600HI	Tube	30	506235

Similar Part	Package	Voltage class
DHG60I600HA	TO-247AD (2)	600
DSEP60-06A	TO-247AD (2)	600
DSEP60-06AT	TO-268AA (D3Pak) (2)	600

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 175^{\circ}\text{C}$



Fast Diode

$V_{0 \max}$ threshold voltage

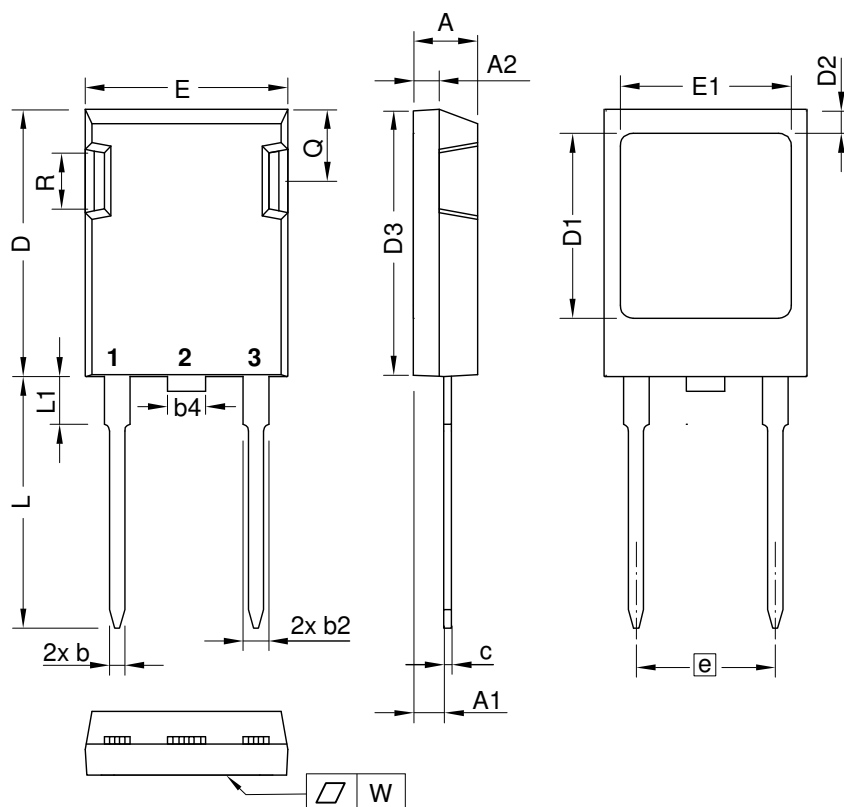
1.1

V

$R_{0 \max}$ slope resistance *

10

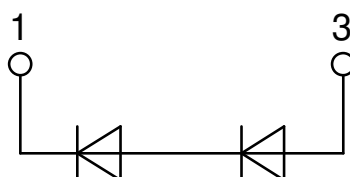
mΩ

Outlines ISOPLUS247


Dim.	Millimeter		Inches	
	min	max	min	max
A	4.83	5.21	0.190	0.205
A1	2.29	2.54	0.090	0.100
A2	1.91	2.16	0.075	0.085
b	1.14	1.40	0.045	0.055
b2	1.91	2.20	0.075	0.087
b4	2.92	3.24	0.115	0.128
c	0.61	0.83	0.024	0.033
D	20.80	21.34	0.819	0.840
D1	15.75	16.26	0.620	0.640
D2	1.65	2.15	0.065	0.085
D3	20.30	20.70	0.799	0.815
E	15.75	16.13	0.620	0.635
E1	13.21	13.72	0.520	0.540
e	10.90	BSC	0.429	BSC
L	19.81	20.60	0.780	0.811
L1	3.81	4.38	0.150	0.172
Q	5.59	6.20	0.220	0.244
R	4.25	5.50	0.167	0.217
W	-	0.10	-	0.004

Die konvexe Form des Substrates ist typ. < 0.04 mm über der Kunststoffoberfläche der Bauteilunterseite
 The convex bow of substrate is typ. < 0.04 mm over plastic surface level of device bottom side

Die Gehäuseabmessungen entsprechen dem Typ TO-247 AD gemäß JEDEC außer Schraubloch und L_{max} .
 This drawing will meet all dimensions requirement of JEDEC outline TO-247 AD except screw hole and except L_{max} .



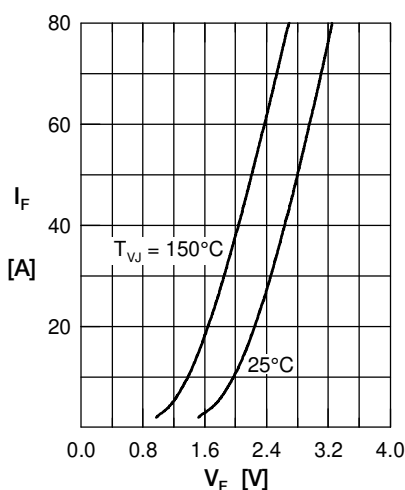
Fast Diode


Fig. 1 Forward current
 I_F versus V_F

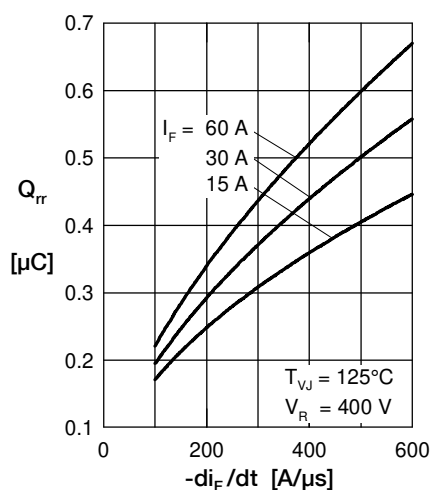


Fig. 2 Typ. reverse recov. charge
 Q_{rr} versus $-di_F/dt$

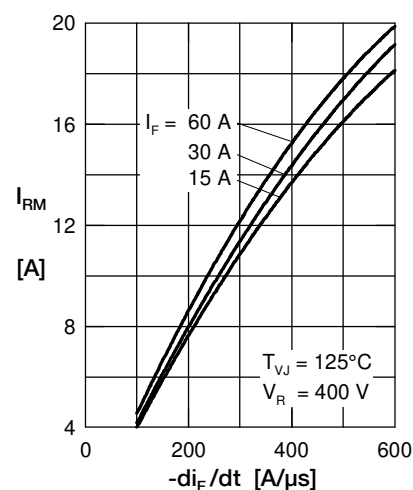


Fig. 3 Typ. reverse recov. current
 I_{RM} versus $-di_F/dt$

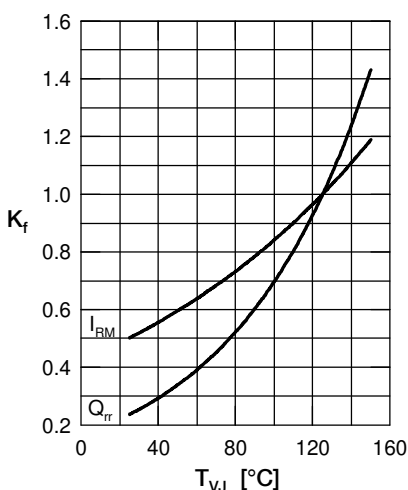


Fig. 4 Typ. dynamic parameters
 Q_{rr} , I_{RM} versus T_{VJ}

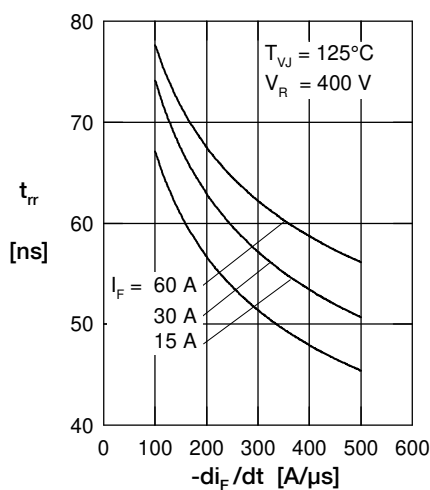


Fig. 5 Typ. reverse recov. time
 t_{rr} versus $-di_F/dt$

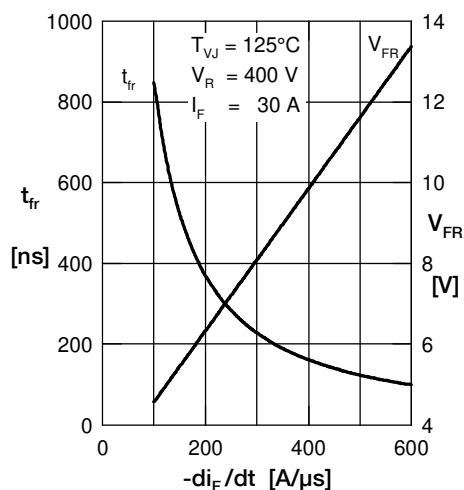


Fig. 6 Typ. forward recov. voltage
 V_{FR} & time t_{fr} versus di_F/dt

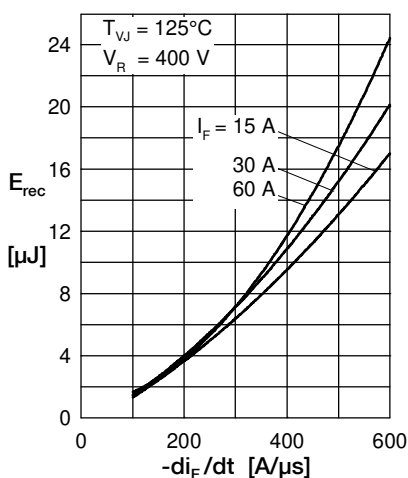


Fig. 7 Typ. recovery energy
 E_{rec} versus $-di_F/dt$

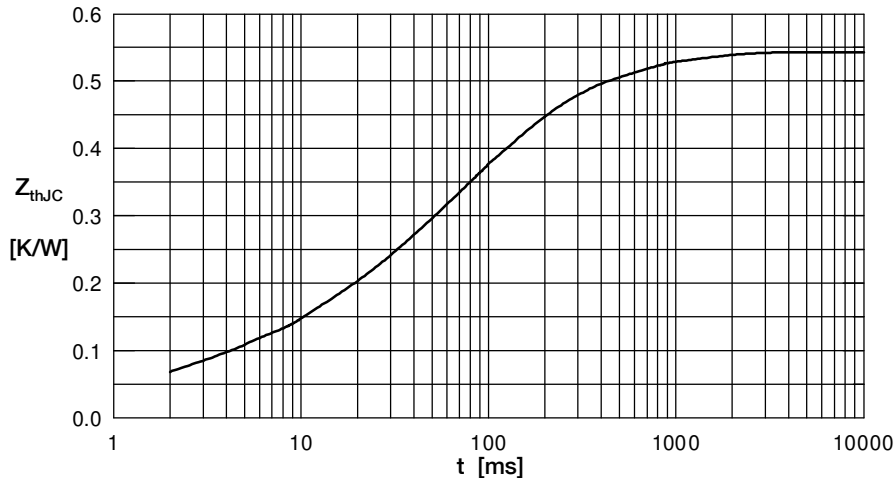


Fig. 8 Transient thermal impedance junction to case